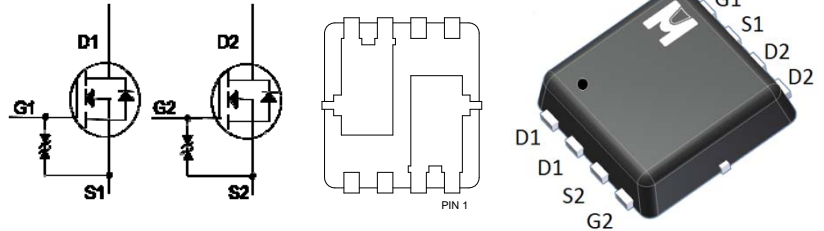


Dual N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV_{DSS}	30V
$R_{DS(on)}$ (MAX.)	21m Ω
I_D	9A



UIS, Rg 100% Tested

Pb-Free Lead Plating & Halogen Free

ESD Protection



ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_A = 25\text{ }^\circ\text{C}$	I_D	9	A
	$T_A = 70\text{ }^\circ\text{C}$		7	
Pulsed Drain Current ¹		I_{DM}	36	
Avalanche Current		I_{AS}	10	
Avalanche Energy	$L = 0.1\text{mH}, I_D = 10\text{A}, R_G = 25\Omega$	E_{AS}	5	mJ
Repetitive Avalanche Energy ²	$L = 0.05\text{mH}$	E_{AR}	2.5	
Power Dissipation	$T_A = 25\text{ }^\circ\text{C}$	P_D	3.1	W
	$T_A = 70\text{ }^\circ\text{C}$		2	
Operating Junction & Storage Temperature Range		T_{j}, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	$R_{\theta JC}$		7.5	$^\circ\text{C} / \text{W}$
Junction-to-Ambient ³	$R_{\theta JA}$		40	

¹Pulse width limited by maximum junction temperature.

²Duty cycle $\leq 1\%$

³40 $^\circ\text{C} / \text{W}$ when mounted on a 1 in² pad of 2 oz copper.



ELECTRICAL CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.5	3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 10	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24V, V_{GS} = 0V$			1	μA
		$V_{DS} = 20V, V_{GS} = 0V, T_J = 125\text{ }^\circ\text{C}$			25	
On-State Drain Current ¹	$I_{D(ON)}$	$V_{DS} = 10V, V_{GS} = 10V$	9			A
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 9A$		18	21	$m\Omega$
		$V_{GS} = 4.5V, I_D = 5A$		24	29	
Forward Transconductance ¹	g_{fs}	$V_{DS} = 5V, I_D = 9A$		16		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 15V, f = 1MHz$		530		pF
Output Capacitance	C_{oss}			102		
Reverse Transfer Capacitance	C_{rss}			81		
Gate Resistance	R_g	$V_{GS} = 15mV, V_{DS} = 0V, f = 1MHz$		2.0		Ω
Total Gate Charge ^{1,2}	$Q_g(V_{GS}=10V)$	$V_{DS} = 15V, V_{GS} = 10V,$ $I_D = 9A$		11		nC
	$Q_g(V_{GS}=4.5V)$			5.7		
Gate-Source Charge ^{1,2}	Q_{gs}			1.7		
Gate-Drain Charge ^{1,2}	Q_{gd}			3		
Turn-On Delay Time ^{1,2}	$t_{d(on)}$		$V_{DS} = 15V,$ $I_D = 1A, V_{GS} = 10V, R_{GS} = 6\Omega$		11	
Rise Time ^{1,2}	t_r			16		
Turn-Off Delay Time ^{1,2}	$t_{d(off)}$			36		
Fall Time ^{1,2}	t_f			20		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_C = 25\text{ }^\circ\text{C}$)						
Continuous Current	I_S				2.3	A
Pulsed Current ³	I_{SM}				9.2	
Forward Voltage ¹	V_{SD}	$I_F = I_S, V_{GS} = 0V$			1.2	V
Reverse Recovery Time	t_{rr}	$I_F = I_S, di_F/dt = 100A / \mu S$		45		nS
Peak Reverse Recovery Current	$I_{RM(REC)}$			28		A
Reverse Recovery Charge	Q_{rr}			3		nC

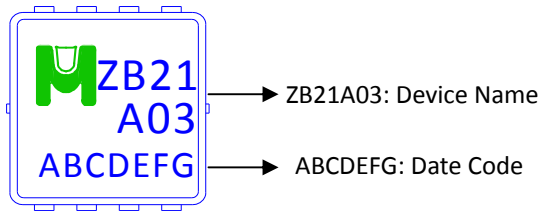
¹Pulse test : Pulse Width $\leq 300 \mu\text{sec}$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

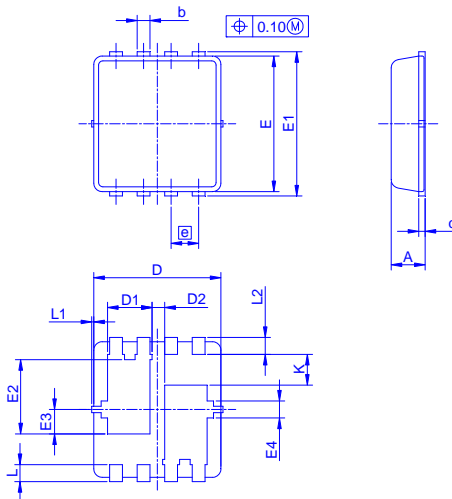
³Pulse width limited by maximum junction temperature.

Ordering & Marking Information:

Device Name: EMZB21A03VG for EDFN 3 x 3



Outline Drawing



Dimension in mm

Dimension	A	A1	b	c	D	D1	D2	E	E1	E2	E3	E4	e	K	L	L1	L2	$\theta 1$
Min.	0.7	0	0.24	0.10	2.90	0.85	0.25	2.90	3.05	1.55	0.43	0.28	0.6	0.45	0.33	0	0.25	0°
Max.	0.9	0.05	0.30	0.25	3.10	1.15	0.45	3.10	3.35	1.95	0.63	0.38	0.7	0.85	0.53	0.10	0.35	12°

Recommended minimum pads

